

MOS FIELD EFFECT TRANSISTORS  
**2SK2361/2SK2362**

SWITCHING  
 N-CHANNEL POWER MOS FET  
 INDUSTRIAL USE

**DESCRIPTION**

The 2SK2361/2SK2362 is N-Channel MOS Field Effect Transistor designed for high voltage switching applications.

**FEATURES**

- Low On-Resistance  
 2SK2361:  $R_{DS(on)} = 0.9 \Omega$  ( $V_{GS} = 10 V, I_D = 5.0 A$ )  
 2SK2362:  $R_{DS(on)} = 1.0 \Omega$  ( $V_{GS} = 10 V, I_D = 5.0 A$ )
- Low  $C_{iss}$   $C_{iss} = 1050 pF$  TYP.
- High Avalanche Capability Ratings

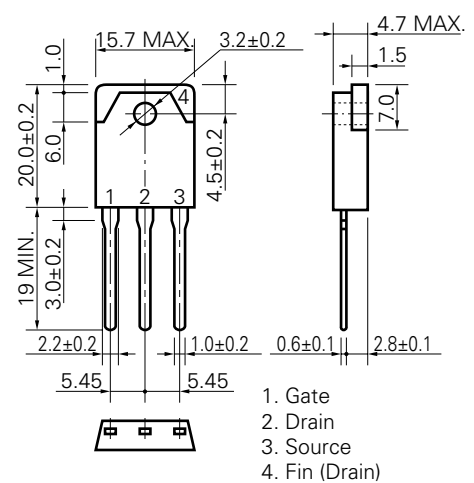
**ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ C$ )**

Drain to Source Voltage (2SK2361/2SK2362)	$V_{BSS}$	450/500	V
Gate to Source Voltage	$V_{GSS}$	$\pm 30$	V
Drain Current (DC)	$I_D(DC)$	$\pm 10$	A
Drain Current (pulse)*	$I_D(pulse)$	$\pm 40$	A
Total Power Dissipation ( $T_c = 25^\circ C$ )	$P_{T1}$	100	W
Total Power Dissipation ( $T_A = 25^\circ C$ )	$P_{T2}$	3.0	W
Channel Temperature	$T_{ch}$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ C$
Single Avalanche Current**	$I_{AS}$	10	A
Single Avalanche Energy**	$E_{AS}$	142	mJ

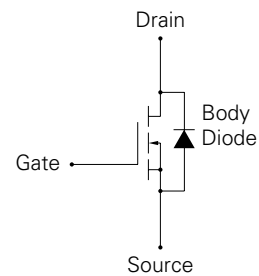
\*  $PW \leq 10 \mu s, Duty Cycle \leq 1 \%$

\*\* Starting  $T_{ch} = 25^\circ C, R_G = 25 \Omega, V_{GS} = 20 V \rightarrow 0$

**PACKAGE DIMENSIONS**  
 (in millimeter)



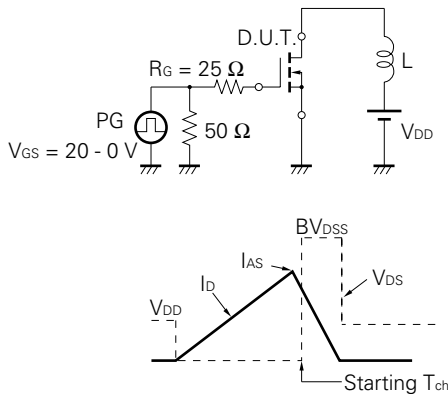
**MP-88**



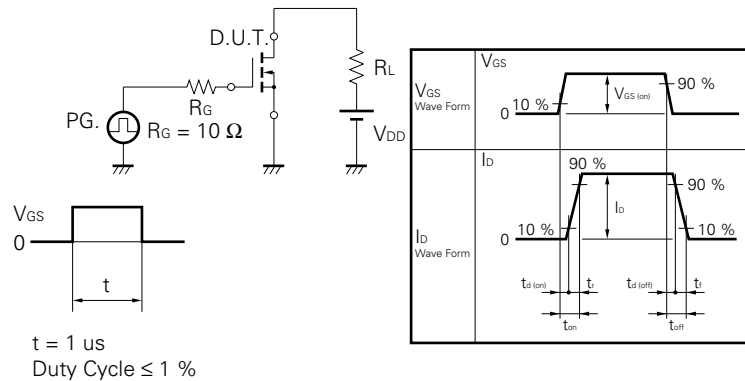
**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C)**

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
Drain to Source On-Resistance	R <sub>DS(on)</sub>		0.7	0.9	Ω	V <sub>GS</sub> = 10 V	2SK2361
			0.8	1.0	Ω	I <sub>D</sub> = 5.0 A	2SK2362
Gate to Source Cutoff Voltage	V <sub>GS(off)</sub>	2.5		3.5	V	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	
Forward Transfer Admittance	y <sub>fs</sub>	3.0			S	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 5.0 A	
Drain Leakage Current	I <sub>bss</sub>			100	μA	V <sub>DS</sub> = V <sub>DSS</sub> , V <sub>GS</sub> = 0	
Gate to Source Leakage Current	I <sub>gss</sub>			±100	nA	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0	
Input Capacitance	C <sub>iss</sub>		1050		pF	V <sub>DS</sub> = 10 V	
Output Capacitance	C <sub>oss</sub>		200		pF	V <sub>GS</sub> = 0	
Reverse Transfer Capacitance	C <sub>rss</sub>		26		pF	f = 1 MHz	
Turn-On Delay Time	t <sub>d(on)</sub>		15		ns	I <sub>D</sub> = 5.0 A	
Rise Time	t <sub>r</sub>		24		ns	V <sub>GS</sub> = 10 V	
Turn-Off Delay Time	t <sub>d(off)</sub>		50		ns	V <sub>DD</sub> = 150 V	
Fall Time	t <sub>f</sub>		14		ns	R <sub>G</sub> = 10 Ω R <sub>L</sub> = 30 Ω	
Total Gate Charge	Q <sub>G</sub>		26		nC	I <sub>D</sub> = 10 A	
Gate to Source Charge	Q <sub>GS</sub>		6.1		nC	V <sub>DD</sub> = 400 V	
Gate to Drain Charge	Q <sub>GD</sub>		12		nC	V <sub>GS</sub> = 10 V	
Body Diode Forward Voltage	V <sub>F(S-D)</sub>		1.0		V	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0	
Reverse Recovery Time	t <sub>rr</sub>		350		ns	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0	
Reverse Recovery Charge	Q <sub>rr</sub>		2.0		μC	di/dt = 50 A/μs	

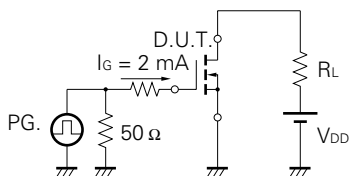
**Test Circuit 1 Avalanche Capability**



**Test Circuit 2 Switching Time**

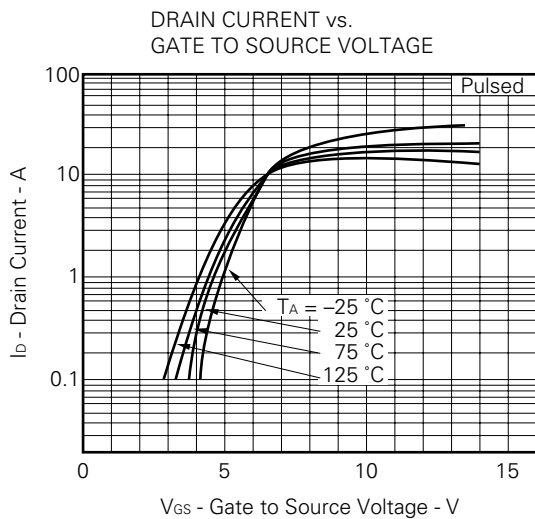
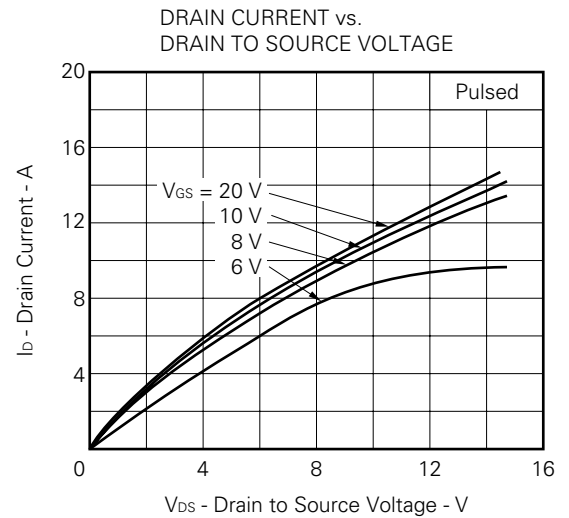
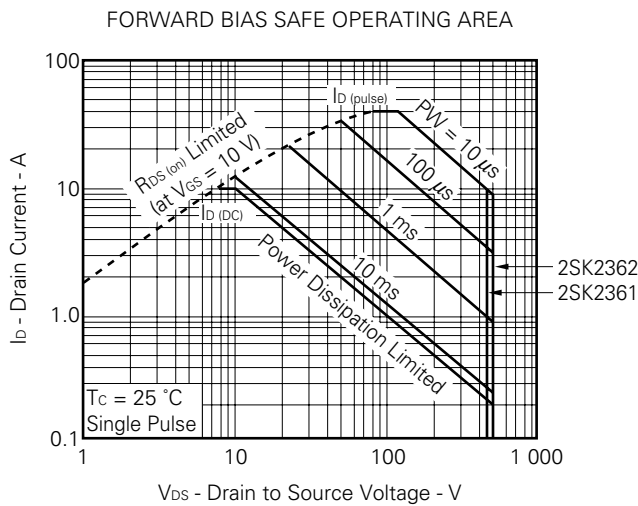
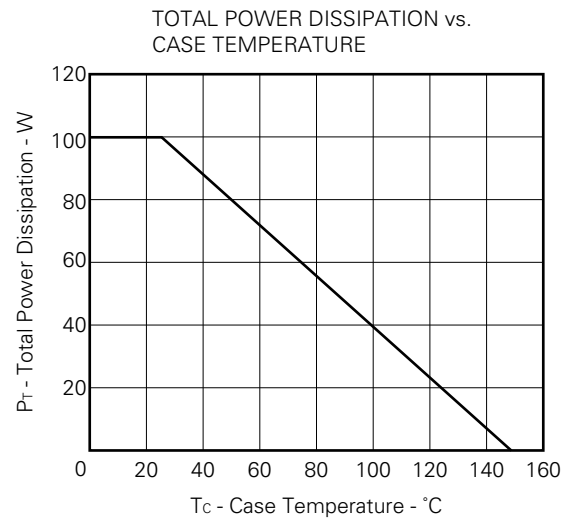
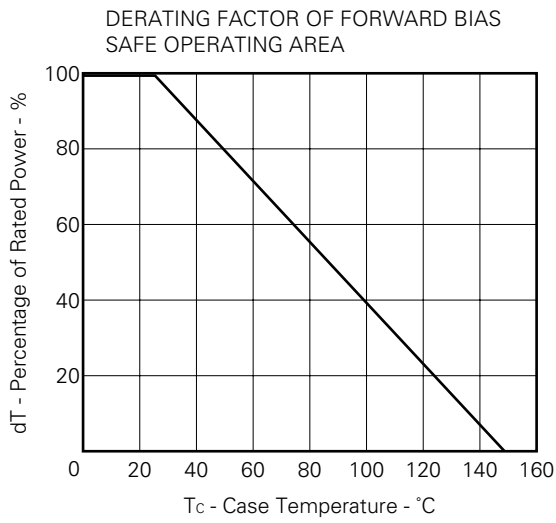


**Test Circuit 3 Gate Charge**

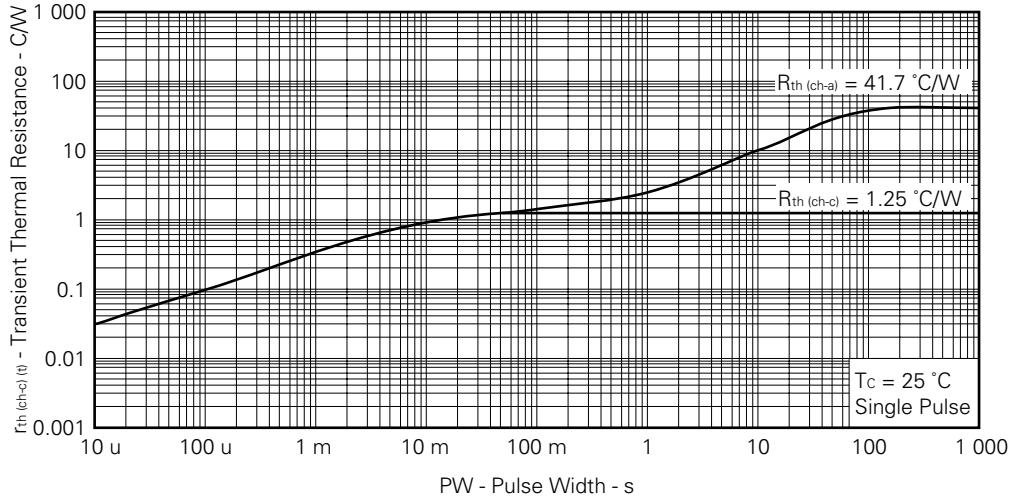


The application circuits and their parameters are for references only and are not intended for use in actual design-in's.

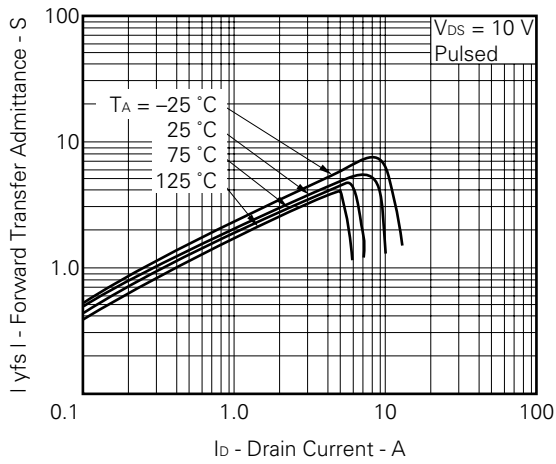
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C)



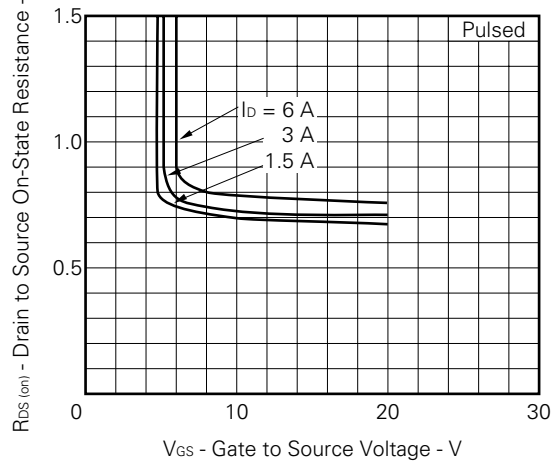
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



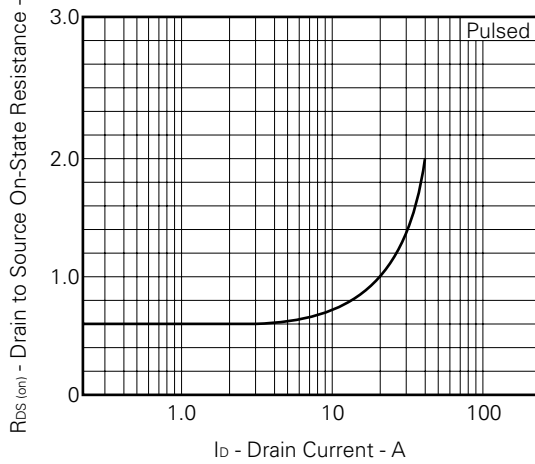
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



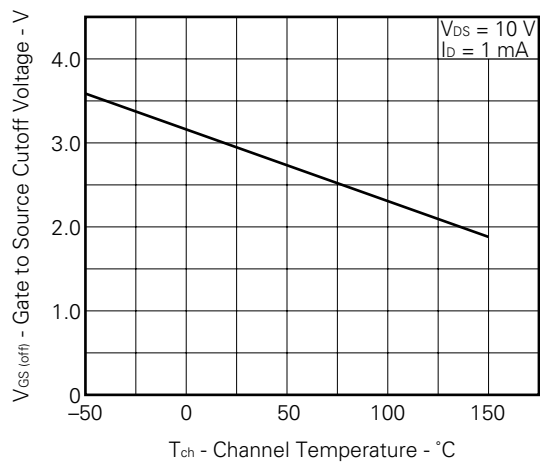
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

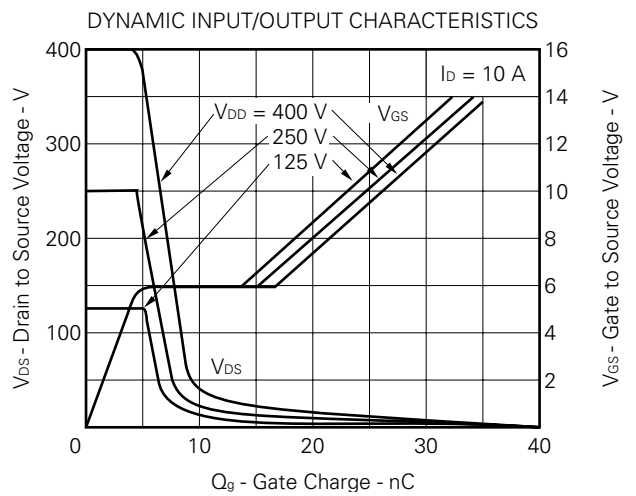
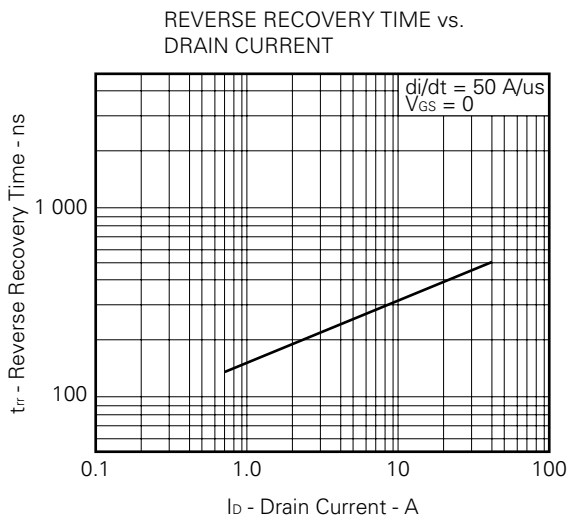
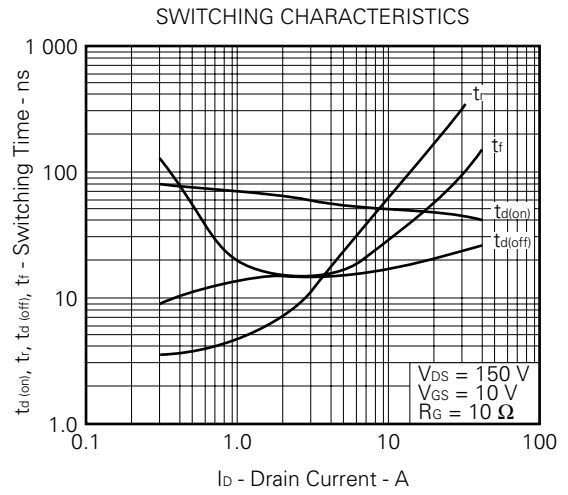
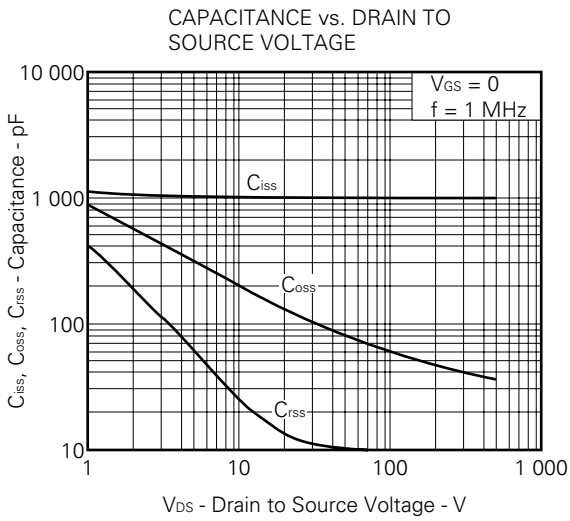
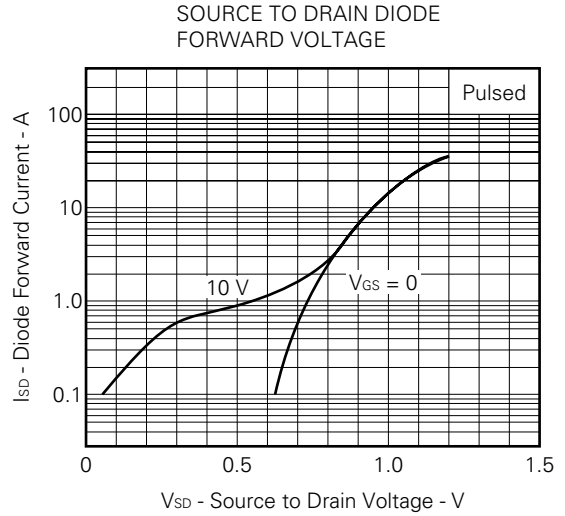
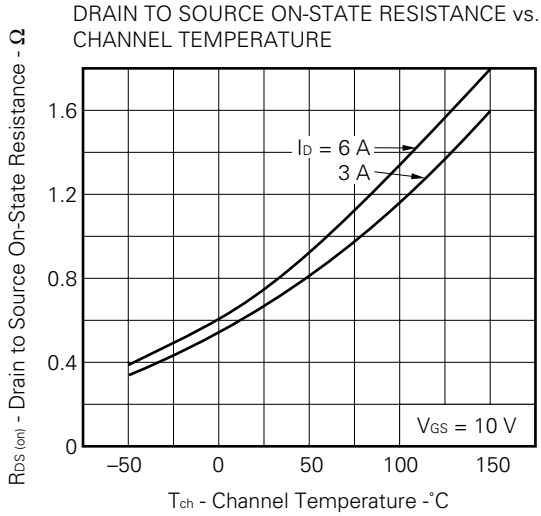


DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

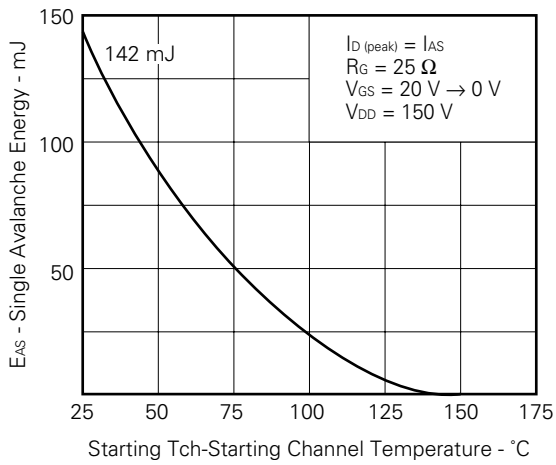


GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE

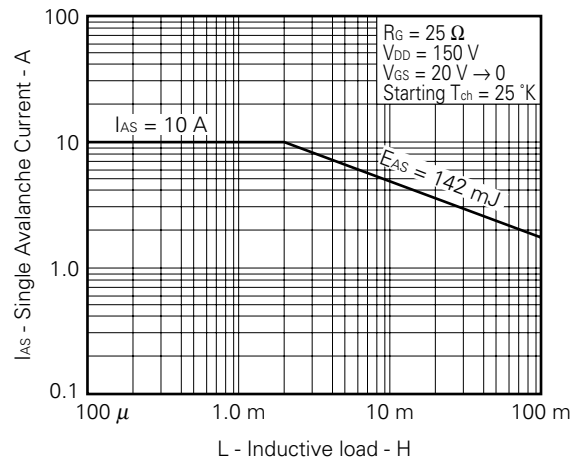




SINGLE AVALANCHE ENERGY vs. STARTING CHANNEL TEMPERATURE



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



**REFERENCE**

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134
Power MOS FET features and application switching power supply.	TEA-1034
Application circuits using Power MOS FET.	TEA-1035
Safe operating area of Power MOS FET.	TEA-1037

The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device is actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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